



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



BAW56L, SBAW56L

Dual Switching Diode Common Anode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Forward Surge Current (60 Hz @ 1 cycle)	I_{FSM}	2.0	A
Non-Repetitive Peak Forward Current $t = 1 \mu\text{s}$ (Note 3)	I_{FSM}	4.0	A
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I_{FRM}	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

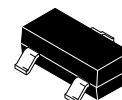
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Square Wave; $T_J = 25^\circ\text{C}$.

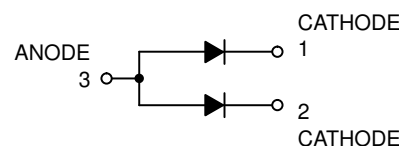


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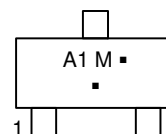
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SOT-23 (TO-236)
CASE 318
STYLE 12



MARKING DIAGRAM



A1 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

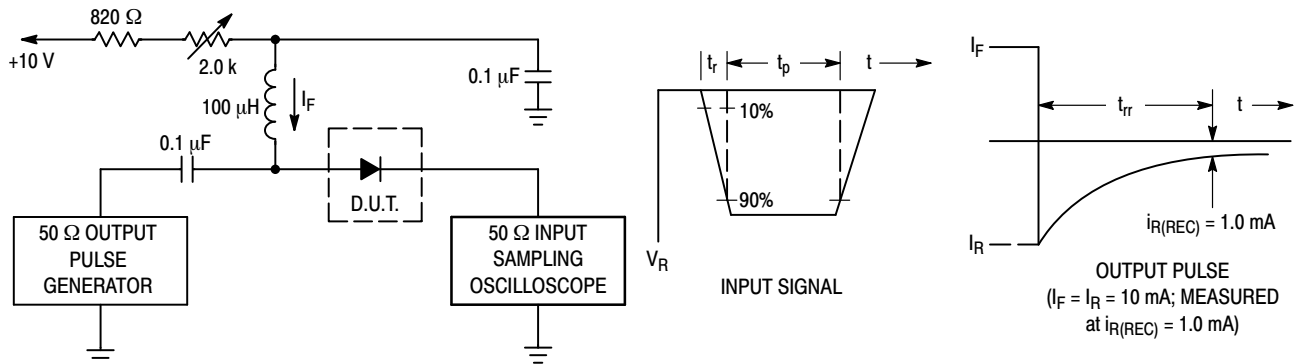
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAW56L, SBAW56L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(BR)}$	70	-	V
Reverse Voltage Leakage Current ($V_R = 25 \text{ V}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{ V}$) ($V_R = 70 \text{ V}$, $T_J = 150^\circ\text{C}$)	I_R	-	30 2.5 50	μA
Diode Capacitance ($V_R = 0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_D	-	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mA}$) ($I_F = 10 \text{ mA}$) ($I_F = 50 \text{ mA}$) ($I_F = 150 \text{ mA}$)	V_F	-	715 855 1000 1250	mV
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$, $I_{R(REC)} = 1.0 \text{ mA}$) (Figure 1) $R_L = 100 \Omega$	t_{rr}	-	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAW56L, SBAW56L

Curves Applicable to Each Cathode

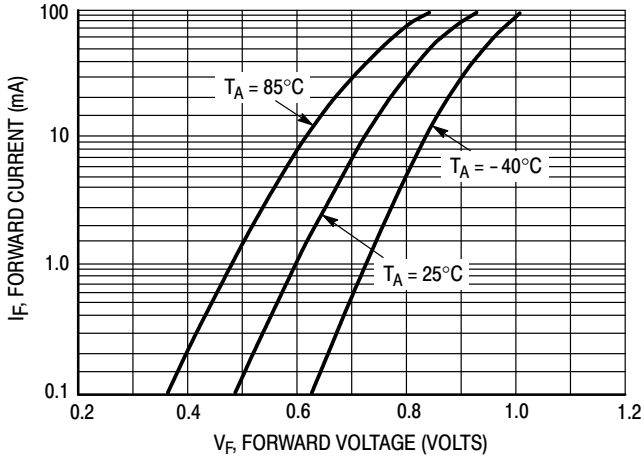


Figure 2. Forward Voltage

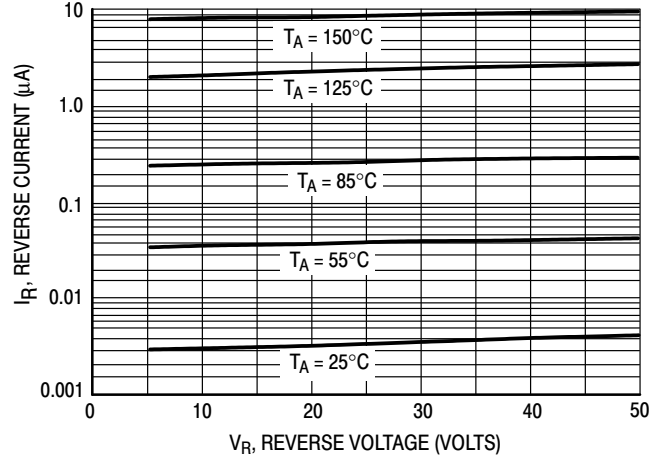


Figure 3. Leakage Current

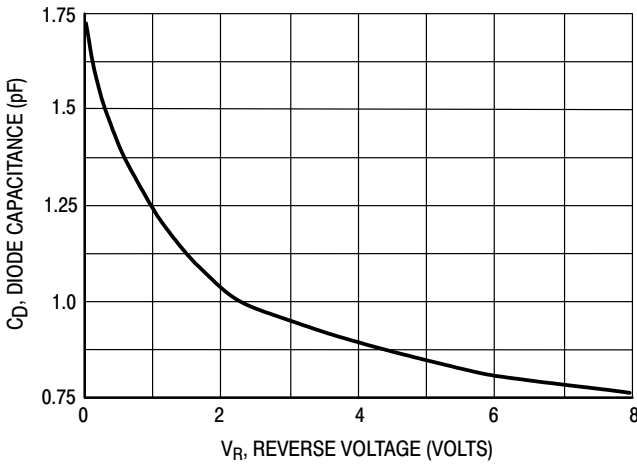


Figure 4. Capacitance

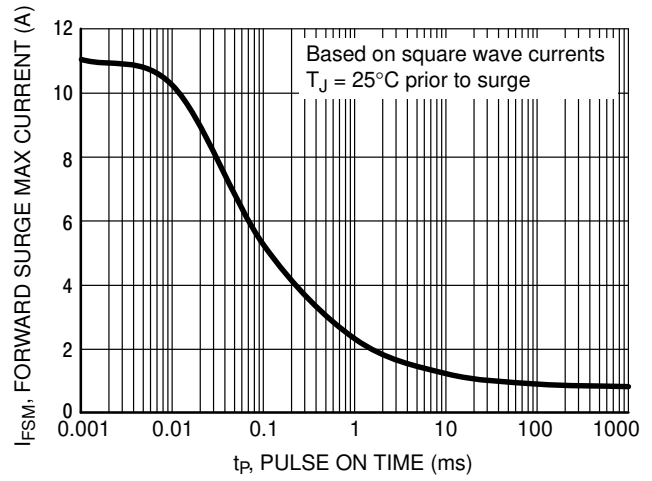
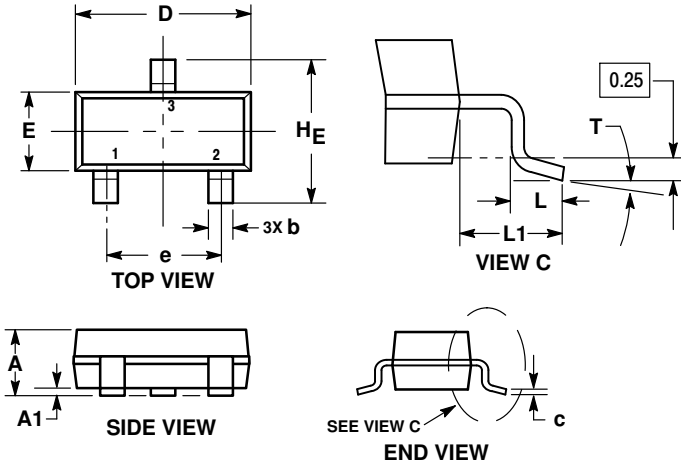


Figure 5. Forward Surge Current

BAW56L, SBAW56L

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

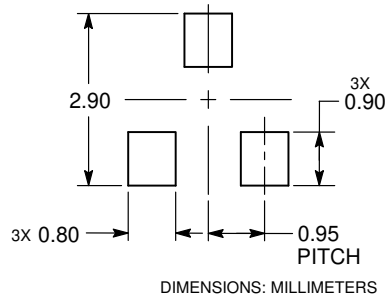
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	—	10°	0°	—	10°

STYLE 12:

- PIN 1. CATHODE
- CATHODE
- ANODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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